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DATE MAILED: 02/18/2005

APPLICATION NO.	FIL	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/635,489	08/07/2003		Mao-Yi Chang	CHAN3214/EM	1409
23364	7590	02/18/2005		EXAMINER	
BACON &		S, PLLC	VU, DAVID		
625 SLATERS LANE FOURTH FLOOR				ART UNIT	PAPER NUMBER
ALEXANDI	UA, VA	22314	2818		

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)					
	10/635,489	CHANG ET AL.					
Office Action Summary	Examiner	Art Unit					
•	DAVID VU	2818					
The MAILING DATE of this communication a							
Period for Reply		,					
A SHORTENED STATUTORY PERIOD FOR REP THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a re - If NO period for reply is specified above, the maximum statutory perio - Failure to reply within the set or extended period for reply will, by statu. Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).	l. 1.136(a). In no event, however, may a reply be timely 1.136(a). In no event, however, may a reply be timely 1.136(a). In no event, however, may a reply be timely 1.136(a). MONTHS from 1.136(a). MONT	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).					
Status							
1) Responsive to communication(s) filed on 08/	<u>′07/03</u> .	·					
·— ·—	nis action is non-final.						
3) Since this application is in condition for allow							
closed in accordance with the practice under	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims							
4)⊠ Claim(s) <u>1-10</u> is/are pending in the application	on.						
	4a) Of the above claim(s) is/are withdrawn from consideration. ☐ Claim(s) is/are allowed. ☐ Claim(s) 1-10 is/are rejected.						
5) Claim(s) is/are allowed.							
6)⊠ Claim(s) <u>1-10</u> is/are rejected.							
7) Claim(s) is/are objected to.							
8) Claim(s) are subject to restriction and	/or election requirement.						
Application Papers							
9) The specification is objected to by the Examin	ner.						
10)⊠ The drawing(s) filed on <u>07 August 2003</u> is/are: a)⊠ accepted or b)□ objected to by the Examiner.							
Applicant may not request that any objection to the	e drawing(s) be held in abeyance. See	e 37 CFR 1.85(a).					
Replacement drawing sheet(s) including the corre							
11) The oath or declaration is objected to by the	Examiner. Note the attached Office	Action or form PTO-152.					
Priority under 35 U.S.C. § 119							
12) Acknowledgment is made of a claim for foreig	an priority under 35 U.S.C. § 119(a))-(d) or (f).					
a)⊠ All b)□ Some * c)□ None of:							
1. Certified copies of the priority docume	nts have been received.						
2. Certified copies of the priority docume	nts have been received in Applicati	on No					
Copies of the certified copies of the pr	iority documents have been receive	ed in this National Stage					
application from the International Bure							
* See the attached detailed Office action for a list	st of the certified copies not receive	ed.					
		•					
Attachment(s)	_						
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 4) Interview Summary (PTO-413) Paper No(s)/Mail Date.							
 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 		Patent Application (PTO-152)					
Paper No(s)/Mail Date 6) Other:							

DETAILED ACTION

Claim Rejections - 35 USC § 112

1. Claim 7 is rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the enablement requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to enable one skilled in the art to which it pertains, or with which it is most nearly connected, to make and/or use the invention. Claim 7 recites "inert gas atom is doped by dry etching". How can doping be done by etching?

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 2. Claims 1-6 and 8-10 are rejected under 35 U. S. C. 102(e) as being anticipated by Yamazaki et al. (US Pat. 6,812,081, herein after Yamazaki).

Application/Control Number: 10/635,489

Art Unit: 2818

Regarding claim 1, Yamazaki discloses a method for transforming an amorphous silicon layer into a polysilicon layer, comprising: providing an amorphous silicon layer, and doping amorphous silicon layer with an inert gas atom; and heating the surface of amorphous silicon substrate by heat treatment or thermal process (col. 2, lines 40-51; col. 4, line 66 through col. 5, line 11).

Regarding claim 2, Yamazaki discloses that inert gas atom is selected from a group consisting of helium, neon, argon, krypton, xenon (col. 7, lines 42-59).

Regarding claim 3, Yamazaki discloses that inert gas atom is argon (col. 2, lines 1-5 & 42-43).

Regarding claim 4, Yamazaki discloses the atom percentage of inert gas atom in amorphous silicon layer is 0.006 (in the range of from 1 to 0.001) {Yamazaki discloses in col. 2, lines 45-46 that the concentration of Ar in the amorphous silicon layer is $3 \times 10^{20} / \text{cm}^3$; therefore $3 \times 10^{20} / \text{cm}^3$ (Ar)/ $5 \times 10^{22} / \text{cm}^3$ (Si) = 0.006}.

Regarding claims 5-6, Yamazaki discloses that inert gas atom is doped by plasma chemical vapor deposition (col. 7, lines 60-67 & 22-27).

Regarding claim 8, Yamazaki discloses that polysilicon substrate is a panel of a liquid crystal display (col. 24, lines 8-14).

Regarding claim 9, Yamazaki discloses that heat treatment is an excimer laser annealing (col. 8, lines 56-59).

Regarding claim 10, Yamazaki discloses that the process window of excimer laser is in the range of from 100 to 400 mJ/cm² (col. 13, line 66 through col. 14, line 1).

Application/Control Number: 10/635,489

Art Unit: 2818

Conclusion

Page 4

Any inquiry concerning this communication or earlier communications from the 3.

examiner should be directed to David Vu whose telephone number is (571) 272-1798. The

examiner can normally be reached on Monday-Friday from 8:00am to 5:00pm. If attempt to

reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can

be reached on (571) 272-1787. The fax phone number for the organization where this application

or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR, Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

David Vu

February 10, 2005.